Precision, Dual, JFET Input Operational Amplifier

■ FEATURES

●Low Input Offset Voltage	V_{IO}=400μV max. V_{IO}=700μV max. (Ta= -40°C to +125°C)
●Low Input Offset Voltage Drift	$\Delta V_{IO}/\Delta T$=5μV/°C max. (Ta= -40°C to +125°C)
●Low Supply Current	Icc=3mA max.
●High Slew Rate	SR=20V/μs typ.
●Wide Bandwidth	ft=7MHz typ.
●Low Noise	en=10nV/√Hz (at f=1kHz typ.)
●Low Input Bias Current	I_B=80pA max. (at Ta=25°C)
●No Phase Reversal	
●RF noise Immunity	
●Guaranteed Temperature	Topr= -40°C to +125°C
●Operating Voltage	Vopr=±4.5V to ±16V
●Package	MSOP8 (VSP8) meet JEDEC MO-187-DA SOP8 JEDEC 150 mil

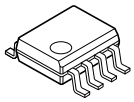
■GENERAL DESCRIPTION

The NJM8512 is a dual high precision JFET input operational amplifier featuring low offset, low offset drift,low bias current, high slew rate, low noise and wide operating temperature range.

The precision performance, high speed and low noise make the NJM8512 especially suitable for filter and amplification of high speed and small signal in instruments, automated test equipment, sensors and other precision applications.

■PACKAGE OUTLINE

NJM8512AR
NJM8512BR
(MSOP8 (VSP8))



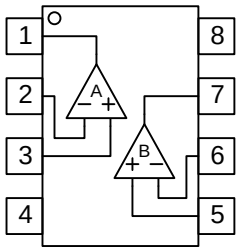
NJM8512AE
NJM8512BE
(SOP8)

■APPLICATIONS

- ●Current Sensor
- ●Photodiode Amplification
- ●Reference Voltage Circuit
- ●Automatic Test Equipment

■PIN CONFIGURATION

(Top View)

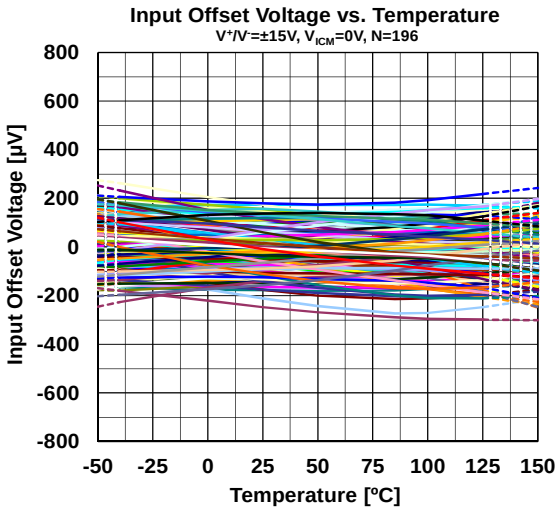


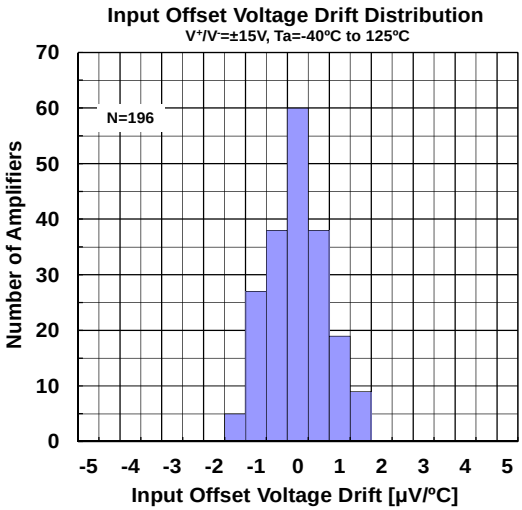
MSOP8(VSP8)
SOP8

PIN FUNCTION

1: OUTPUT A
2: –INPUT A
3: +INPUT A
4: V^-
5: +INPUT B
6: -INPUT B
7: OUTPUT B
8: V^+

■ ELECTRICAL CHARACTERISTICS



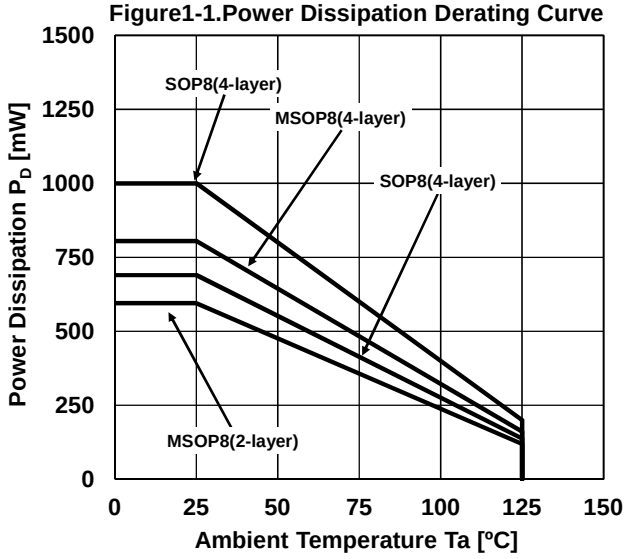


■ ABSOLUTE MAXIMUM RATINGS (Ta=25ºC, unless otherwise noted.)

PARAMETER	SYMBOL	RATING	UNIT
Supply Voltage	V^+/V^-	±18	V
Differential Input Voltage	V_{ID}	±36 (**Note1**)	V
Input Voltage	V_{IN}	V^- - 0.3 to V^+ + 0.3(Note2)	V
Input Current	I_{IN}	±10(Note3)	mA
Power Dissipation MSOP8 (VSP8) SOP8	P_D	(2-layer / 4-layer) 595(Note4) / 805 (Note4) 690 (Note4) / 1000 (Note4)	mW
Output Short-Circuit Duration		Infinete(Ta≦25°C) (Note4)	
Operating Temperature Range	T_{opr}	-40 to +125	ºC
Storage Temperature Range	T_{stg}	-65 to +150	ºC

(Note1) Differential Input Voltage is the voltage difference between +INPUT and -INPUT.
(Note2) The normal operation will establish when any input is within the Common Mode Input Voltage Range of electrical characteristics.
(Note3) If the input voltage exceeds the supply voltage,the input current must be limited 10 mA or less by using a restriction resistance.
(Note4) 2-layer : EIA/JEDEC STANDARD Test board (76.2 x 114.3 x 1.6mm, 2layers, FR-4) mounting.
4-layer : EIA/JEDEC STANDARD Test board (76.2 x 114.3 x 1.6mm, 4layers, FR-4) mounting.
See Figure "Fig.1-1 : Power Dissipation Curve" when ambient temperature is over 25°C.

Figure1-1.Power Dissipation Derating Curve



■RECOMMENDED OPERATING VOLTAGE (Ta=25ºC)

PARAMETER	SYMBOL	RATING	MIN.	TYP.	MAX.	UNIT
Supply Voltage	V^+/V^-		±4.5	-	±16	V

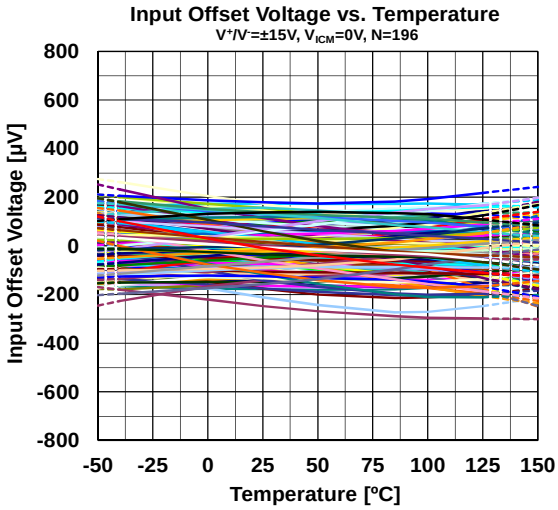
■ ELECTRICAL CHARACTERISTICS (V^+/V^-=±15V, Ta=25°C, V_{ICM}=0V, unless otherwise noted.)

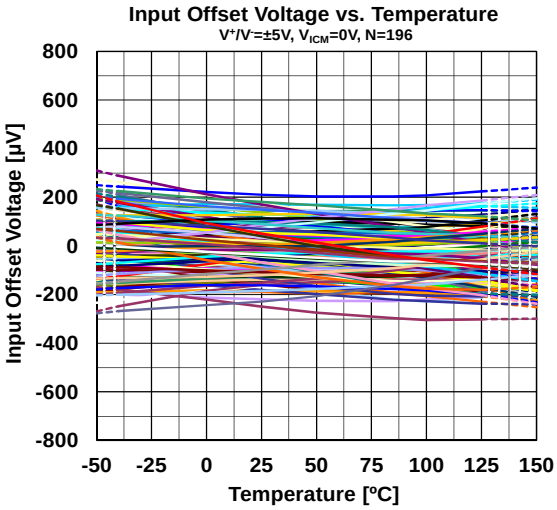
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Characteristics						
Input Offset Voltage						
NJM8512BR/NJM8512BE	$V_{IO}1$		-	80	400	µV
	$V_{IO}2$	Ta = -40ºC to 125ºC	-	-	700	µV
NJM8512AR/NJM8512AE	$V_{IO}1$		-	80	800	µV
	$V_{IO}2$	Ta = -40ºC to 125ºC	-	-	1400	µV
Input Offset Voltage Drift						
NJM8512BR/NJM8512BE	ΔVio/ΔT	Ta = -40ºC to 125ºC	-	0.8	5	µV/ºC
NJM8512AR/NJM8512AE	ΔVio/ΔT	Ta = -40ºC to 125ºC	-	1	9	µV/ºC
Input Bias Current	I_B1		-	25	80	pA
	I_B2	Ta = -40ºC to 125ºC	-	-	35	nA
Input Offset Current	$I_{IO}1$		-	6	75	pA
	$I_{IO}2$	Ta = -40ºC to 125ºC	-	-	2	nA
Common Mode Input Voltage Range	$V_{ICM}1$	CMR ≧ 86dB	-12.5	-	+12.5	V
	$V_{ICM}2$	CMR ≧ 80dB, Ta = -40ºC to 125ºC	-12.5	-	+12.5	V
Common Mode Rejection Ratio	CMR1	V_{CM}=-12.5V to +12.5V	86	108	-	dB
	CMR2	V_{CM}=-12.5V to +12.5V, Ta = -40ºC to 125ºC	80	-	-	dB
	CMR3	V_{CM}=-10V to +10V	100	120	-	dB
Voltage Gain	A_V1	R_L=2kΩ, V_O=-13.5V to +13.5V	90	100	-	dB
	A_V2	R_L=2kΩ, V_O=-13.5V to +13.5V, Ta = -40ºC to 125ºC	82	-	-	dB
	A_V3	R_L=10kΩ, V_O=-13.5V to +13.5V	98	106	-	dB
Input capacitance	C_{IN}		-	10	-	pF
Channel Separation	CS	DC	-	125	-	dB
Output Characteristics						
Maximum Output Voltage	$V_{OH}1$	R_L=10kΩ, Ta = -40ºC to 125ºC	+14.0	+14.2	-	V
	$V_{OL}1$	R_L=10kΩ, Ta = -40ºC to 125ºC	-	-14.9	-14.6	V
	$V_{OH}2$	R_L=2kΩ, Ta = -40ºC to 125ºC	+13.8	+14.1	-	V
	$V_{OL}2$	R_L=2kΩ, Ta = -40ºC to 125ºC	-	-14.8	-14.4	V
	$V_{OH}31$	R_L=600Ω	+13.5	+13.9	-	V
	$V_{OH}32$	R_L=600Ω, Ta = -40ºC to 125ºC	+11.4	-	-	V
	$V_{OL}41$	R_L=600Ω	-	-14.3	-13.8	V
	$V_{OL}42$	R_L=600Ω, Ta = -40ºC to 125ºC	-	-	-12.1	V
Supply Characteristics						
Supply Current	$I_{CC}1$	G_V=+1, R_L=∞	-	2.6	3.0	mA
	$I_{CC}2$	G_V=+1, R_L=∞, Ta = -40ºC to 125ºC	-	-	3.3	mA
Supply Voltage Rejection Ratio	SVR1	V^+/V^- = ±4.5V to ±16V	86	110	-	dB
	SVR2	V^+/V^- = ±4.5V to ±16V, Ta = -40ºC to 125ºC	80	-	-	dB
Dynamic Performance						
Unity Gain Frequency	fT	G_V=+100, R_L=2kΩ, C_L=10pF	-	7	-	MHz
Slew Rate	+SR	RISE, G_V=+1, V_{IN}=1Vpp, R_L=2kΩ	-	20	-	V/µs
	-SR	FALL, G_V=+1, V_{IN}=1Vpp, R_L=2kΩ	-	20	-	V/µs
Settling Time	ts1	To 0.1%, 0V to 10V step, Gv=+1	-	0.7	-	µs
	ts2	To 0.01%, 0V to 10V step, Gv=+1	-	1.0	-	µs
Phase Margin	Φ_M		-	70	-	deg
Total Harmonic Distortion	THD	fo=1kHz, G_V=+1, R_L=2kΩ	-	0.0004	-	%
Noise Performance						
Input Voltage Noise Density	V_{NI}	fo=0.1Hz to 10Hz	-	0.9	-	µVpp
	en1	fo=10Hz	-	20	-	nV/√Hz
	en2	fo=100Hz	-	11	-	nV/√Hz
	en3	fo=1kHz	-	10	-	nV/√Hz
	en4	fo=10kHz	-	9	-	nV/√Hz

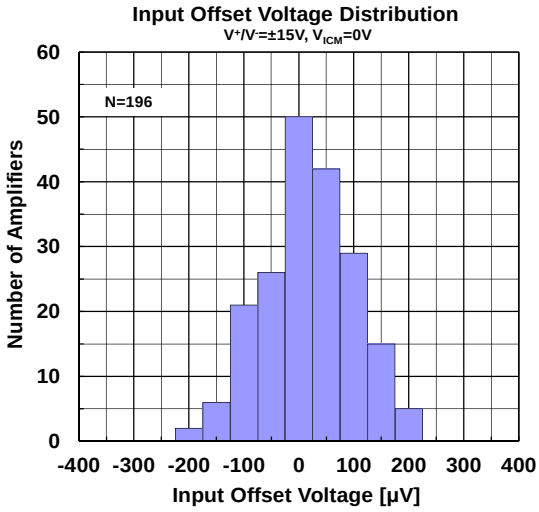
■ELECTRICAL CHARACTERISTICS (V^+/V^-=±5V, Ta=25°C, V_{ICM}=0V, unless otherwise noted.)

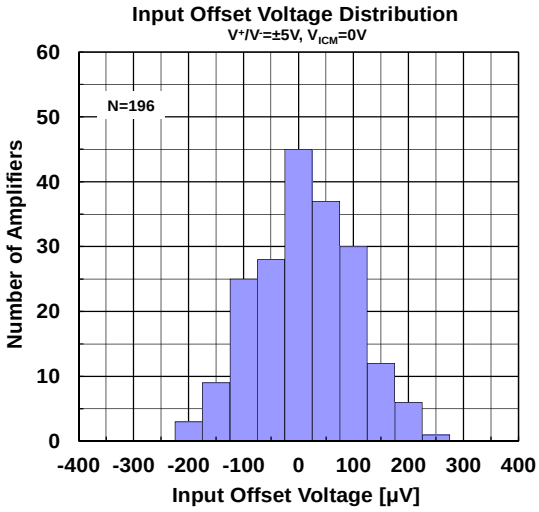
PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Input Characteristics						
Input Offset Voltage						
NJM8512BR/NJM8512BE	$V_{IO}1$		-	80	400	μV
	$V_{IO}2$	Ta = -40°C to 125°C	-	-	700	μV
NJM8512AR/NJM8512AE	$V_{IO}1$		-	80	800	μV
	$V_{IO}2$	Ta = -40°C to 125°C	-	-	1400	μV
Input Offset Voltage Drift						
NJM8512BR/NJM8512BE	ΔVio/ΔT	Ta = -40°C to 125°C	-	0.8	5	μV/°C
NJM8512AR/NJM8512AE	ΔVio/ΔT	Ta = -40°C to 125°C	-	1	9	μV/°C
Input Bias Current	I_B1		-	21	75	pA
	I_B2	Ta = -40°C to 125°C	-	-	31	nA
Input Offset Current	$I_{IO}1$		-	5	50	pA
	$I_{IO}2$	Ta = -40°C to 125°C	-	-	2	nA
Common Mode Input Voltage Range	$V_{ICM}1$	CMR ≧ 86dB	-2	-	+2.5	V
	$V_{ICM}2$	CMR ≧ 80dB, Ta = -40°C to 125°C	-2	-	+2.5	V
Common Mode Rejection Ratio	CMR1	V_{CM}=-2V to +2.5V	86	108	-	dB
	CMR2	V_{CM}=-2V to +2.5V, Ta = -40°C to 125°C	80	-	-	dB
	CMR3	VCM=-1V to +2V	92	113	-	dB
Voltage Gain	A_V1	R_L=2kΩ, V_O=-3V to +3V	85	93	-	dB
	A_V2	R_L=2kΩ, V_O=-3V to +3V, Ta = -40°C to 125°C	80	-	-	dB
	A_V3	RL=10kΩ, V_O=-3V to +3V	90	100	-	dB
Input capacitance	C_{IN}		-	10	-	pF
Channel Separation	CS	DC	-	125	-	dB
Output Characteristics						
Maximum Output Voltage	$V_{OH}1$	R_L=10kΩ, Ta = -40°C to 125°C	+4.1	+4.3	-	V
	$V_{OL}1$	R_L=10kΩ, Ta = -40°C to 125°C	-	-4.9	-4.7	V
	$V_{OH}2$	R_L=2kΩ, Ta = -40°C to 125°C	+3.9	+4.2	-	V
	$V_{OL}2$	R_L=2kΩ, Ta = -40°C to 125°C	-	-4.9	-4.5	V
	$V_{OH}31$	R_L=600Ω	+3.7	+4.1	-	V
	$V_{OH}32$	R_L=600Ω, Ta = -40°C to 125°C	+3.6	-	-	V
	$V_{OL}41$	R_L=600Ω	-	-4.8	-4.3	V
	$V_{OL}42$	R_L=600Ω, Ta = -40°C to 125°C	-	-	-4.2	V
Supply Characteristics						
Supply Current	$I_{CC}1$	G_V=+1, R_L=∞	-	2.0	3.0	mA
	$I_{CC}2$	G_V=+1, R_L=∞, Ta = -40°C to 125°C	-	-	3.3	mA
Dynamic Performance						
Unity Gain Frequency	fT	G_V=+100, R_L=2kΩ, C_L=10pF	-	7	-	MHz
Slew Rate	+SR	RISE, G_V=+1, V_{IN}=1Vpp, R_L=2kΩ	-	18	-	V/μs
	-SR	FALL, G_V=+1, V_{IN}=1Vpp, R_L=2kΩ	-	18	-	V/μs
Settling Time	ts1	To 0.1%, 0V to 4V step, Gv=+1	-	0.5	-	μs
Phase Margin	Φ_M		-	65	-	deg
Total Harmonic Distortion	THD	fo=1kHz, G_V=+1, R_L=2kΩ	-	0.0005	-	%
Noise Performance						
Input Voltage Noise Density	V_{NI}	fo=0.1Hz to 10Hz	-	0.9	-	μVpp
	en1	fo=10Hz	-	20	-	nV/√Hz
	en2	fo=100Hz	-	11	-	nV/√Hz
	en3	fo=1kHz	-	10	-	nV/√Hz
	en4	fo=10kHz	-	9	-	nV/√Hz

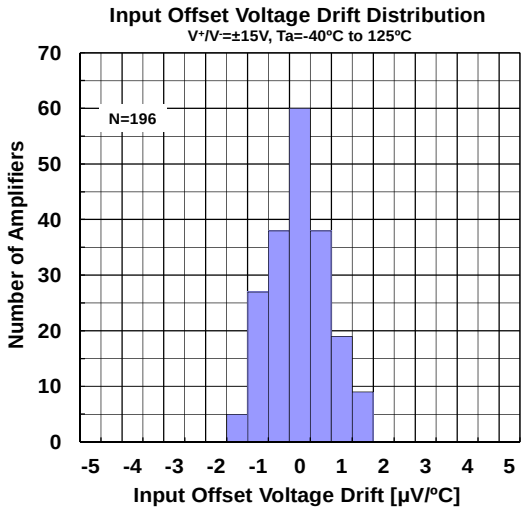
■ ELECTRICAL CHARACTERISTICS

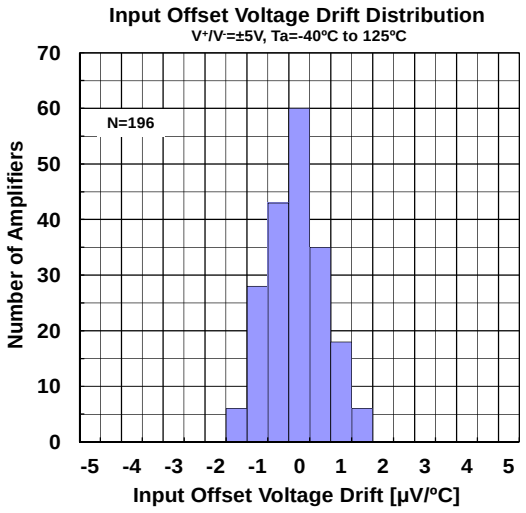






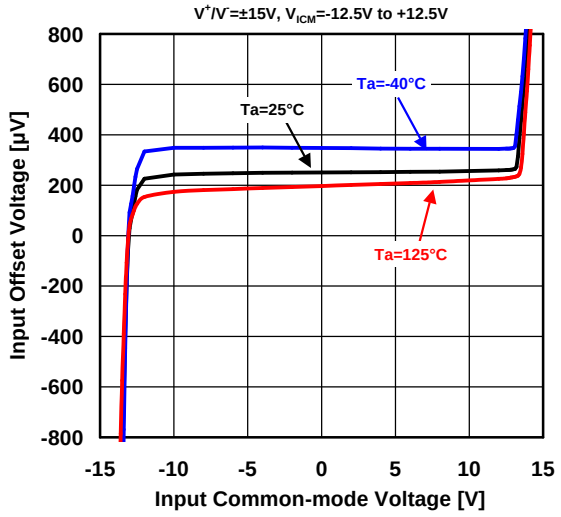






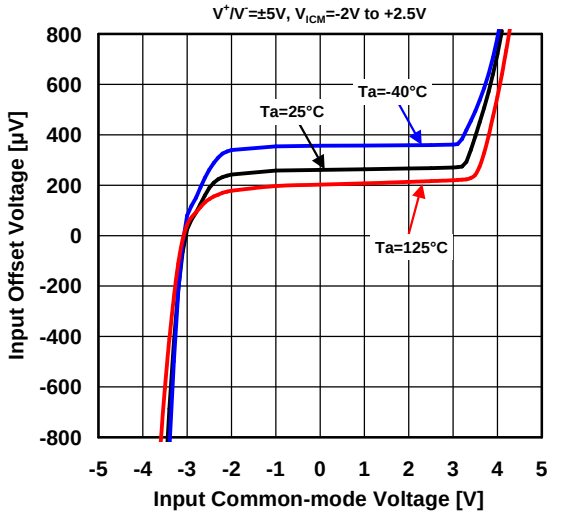
Input Offset Voltage vs. Common-mode Voltage

V^+/V^-=±15V, V_{ICM}=-12.5V to +12.5V

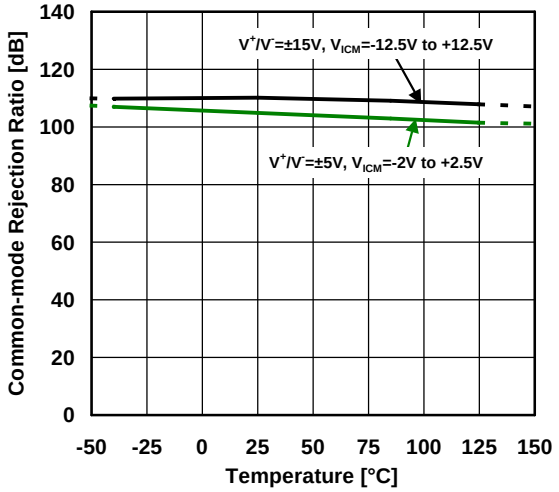


Input Offset Voltage vs. Common-mode Voltage

V^+/V^-=±15V, V_{ICM}=-2V to +2.5V

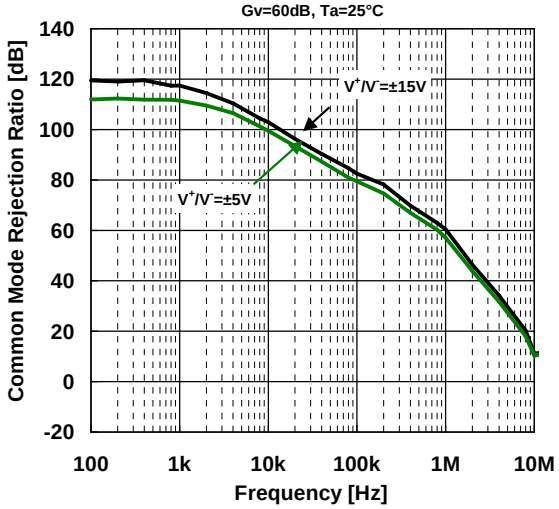


Common-mode Rejection Ratio vs. Temperature



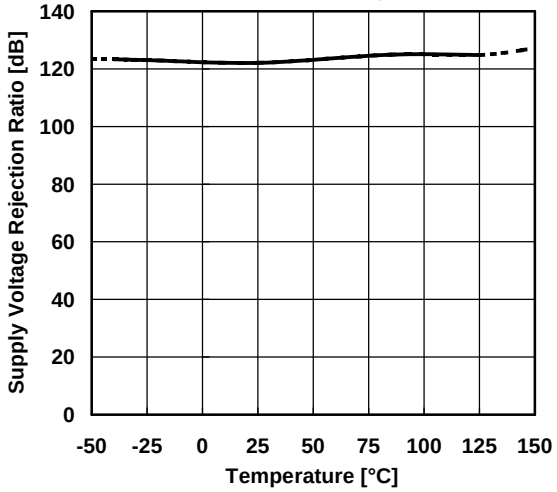
CMR vs. Frequency

Gv=60dB, Ta=25°C



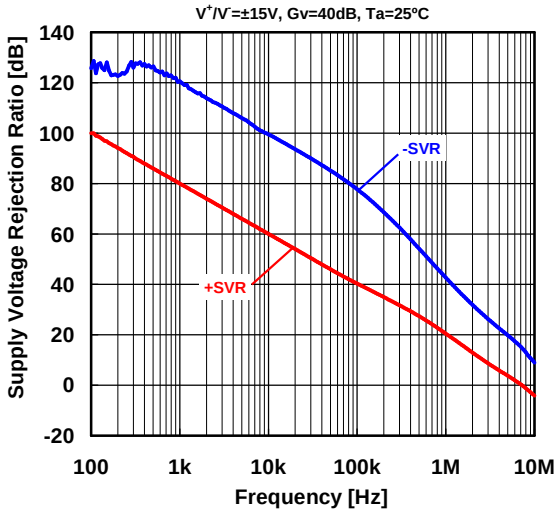
Supply Voltage Rejection Ratio vs. Temperature

V^+/V^-=±4.5V to ±16V, V_{ICM}=0V



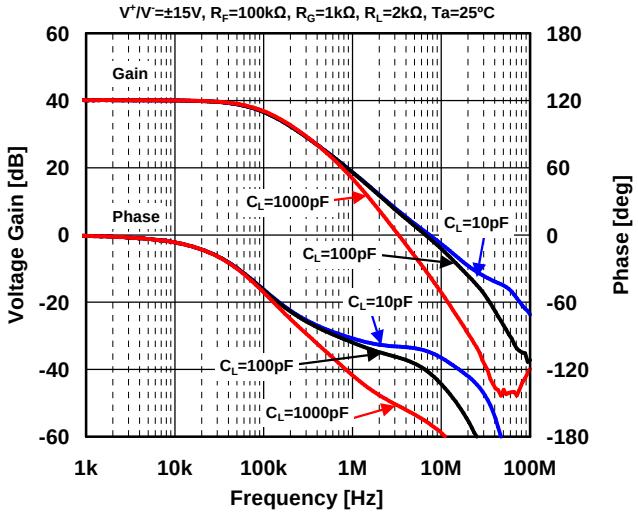
Supply Voltage Rejection Ratio vs. Frequency

V^+/V^-=±15V, Gv=40dB, Ta=25°C



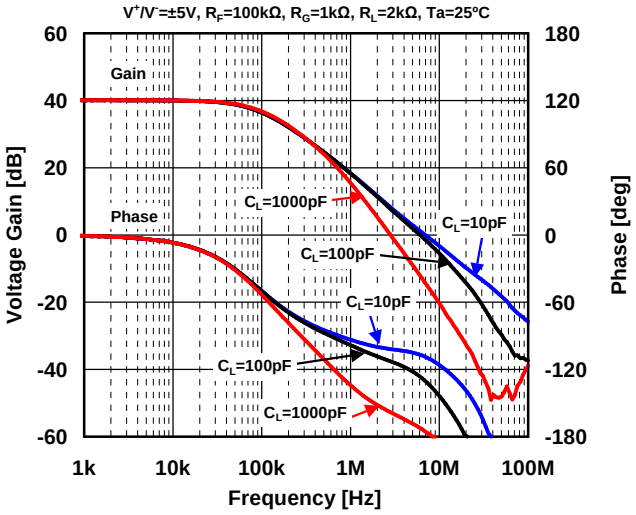
Gain/Phase vs. Frequency

V^+/V^-=±15V, R_F=100kΩ, R_G=1kΩ, R_L=2kΩ, Ta=25°C



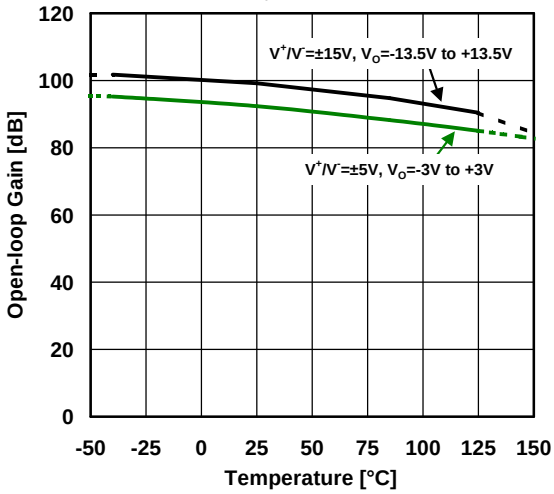
Gain/Phase vs. Frequency

V^+/V^-=±5V, R_F=100kΩ, R_G=1kΩ, R_L=2kΩ, Ta=25°C



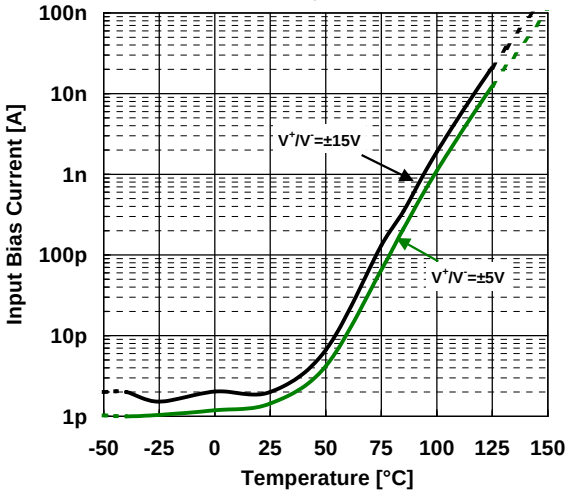
Open-loop Gain vs. Temperature

V_{ICM}=0V, R_L=2kΩ



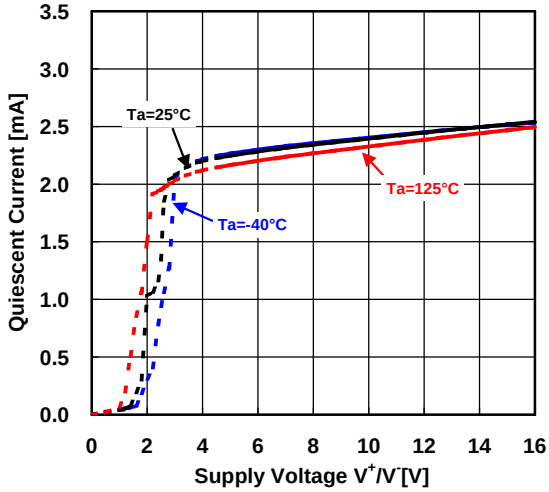
Input Bias Current vs. Temperature

V_{ICM}=0V



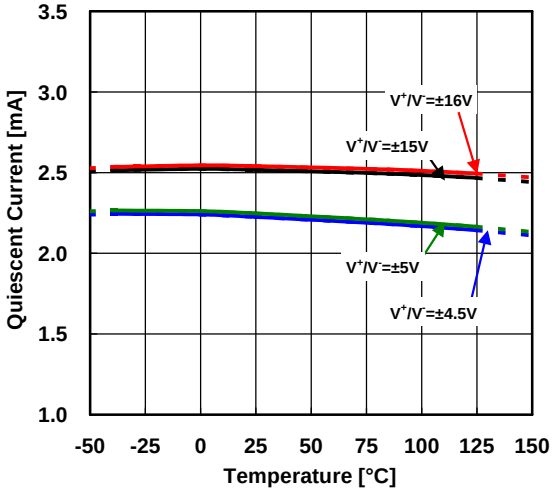
Quiescent Current vs. Supply Voltage

Gv=0dB, V_{ICM}=0V



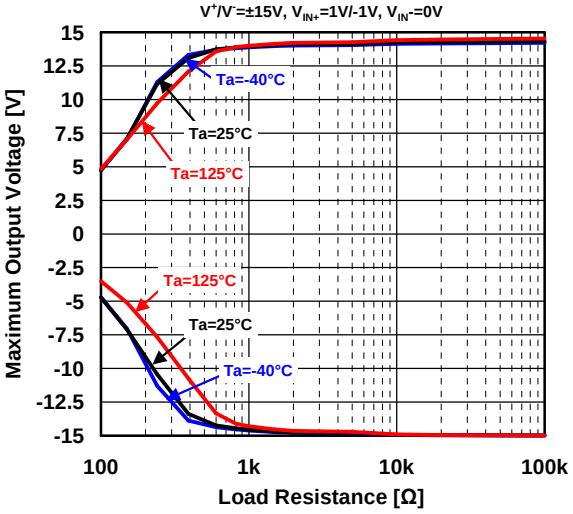
Quiescent Current vs. Temperature

G_V=0dB, V_{ICM}=0V



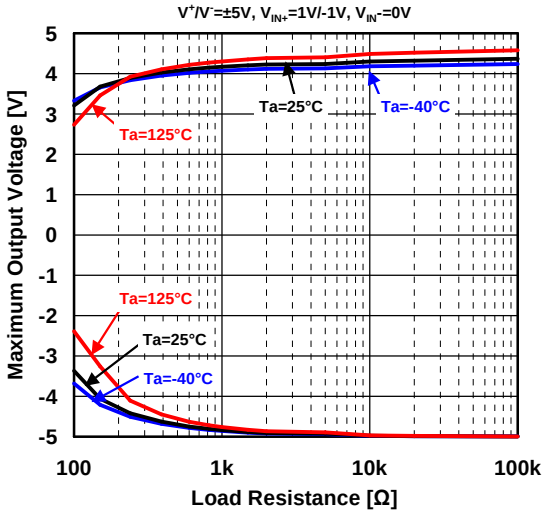
Maximum Output Voltage vs. Load Resistance

V^+/V^-=±15V, V_{IN+}=1V/-1V, V_{IN-}=0V



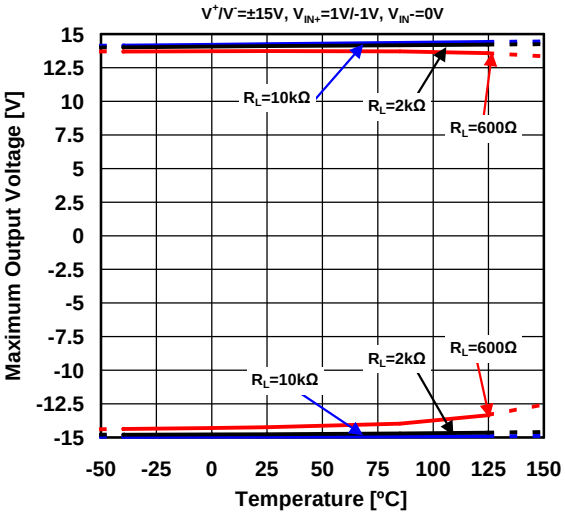
Maximum Output Voltage vs. Load Resistance

V^+/V^-=±5V, V_{IN+}=1V/-1V, V_{IN-}=0V



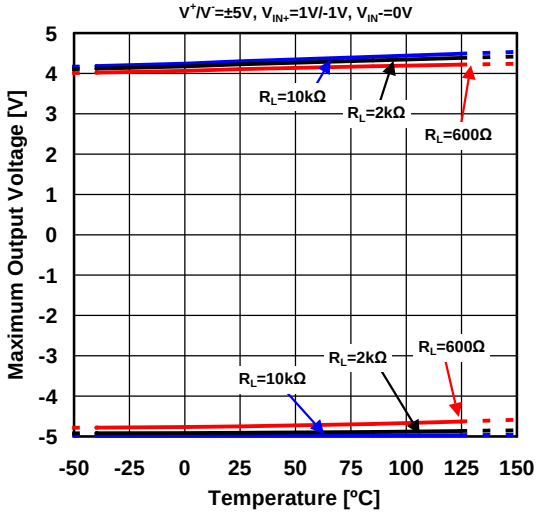
Maximum Output Voltage vs. Temperature

V^+/V^-=±15V, V_{IN+}=1V/-1V, V_{IN-}=0V



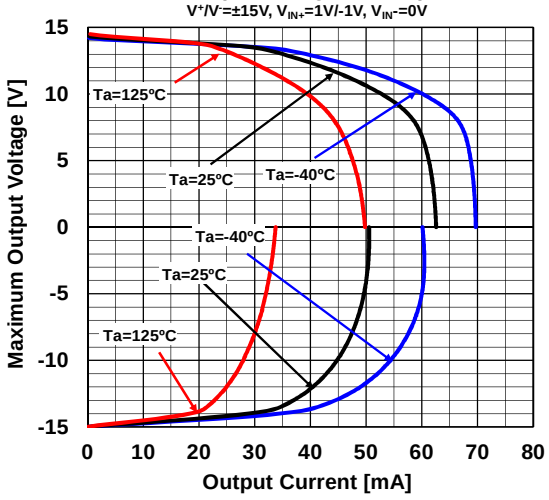
Maximum Output Voltage vs. Temperature

V^+/V^-=±5V, V_{IN+}=1V/-1V, V_{IN-}=0V



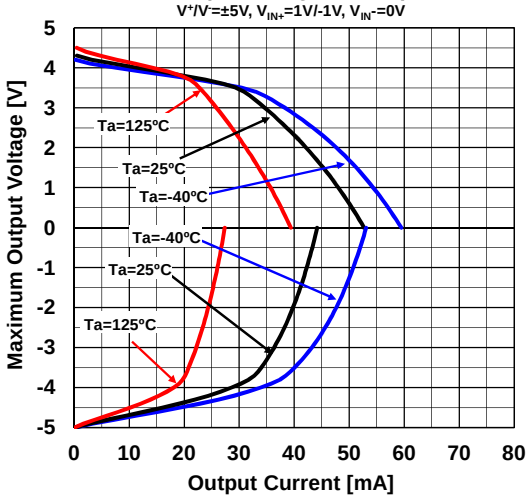
Maximum Output Voltage vs. Output Current

V^+/V^-=±15V, V_{IN+}=1V/-1V, V_{IN-}=0V



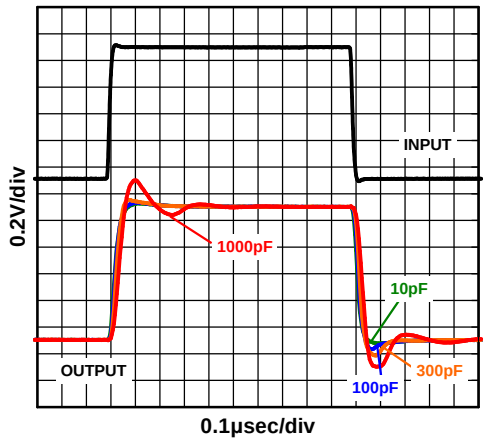
Maximum Output Voltage vs. Output Current

V^+/V^-=±5V, V_{IN+}=1V/-1V, V_{IN-}=0V



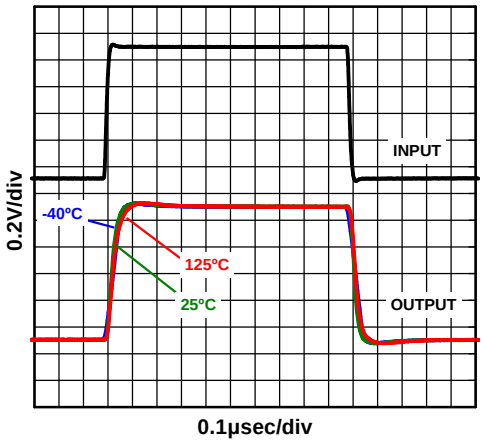
Small-Signal Step Response (Road Capacitance)

V^+/V^-=±15V, Gv=0dB, V_{IN}=1V_{PP}, R_L=2kΩ, Ta=25ºC



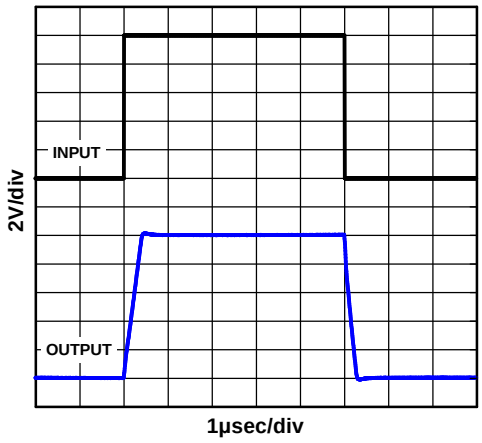
Small-Signal Step Response (Temperature)

V^+/V^-=±15V, Gv=0dB, V_{IN}=1V_{PP}, R_L=2kΩ, C_L=10pF



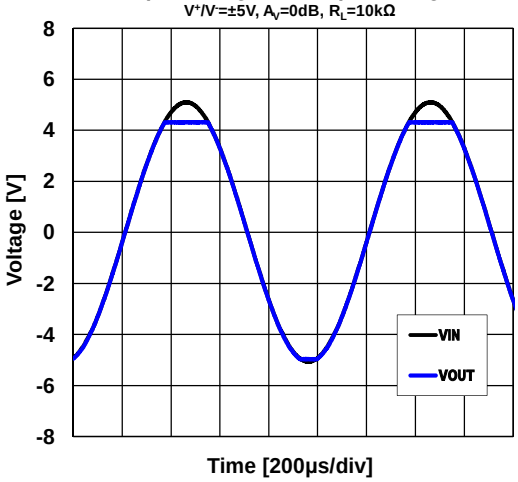
Large Signal Step Response

V^+/V^-=±15V, Gv=0dB, V_{IN}=10Vpp, R_L=2kΩ



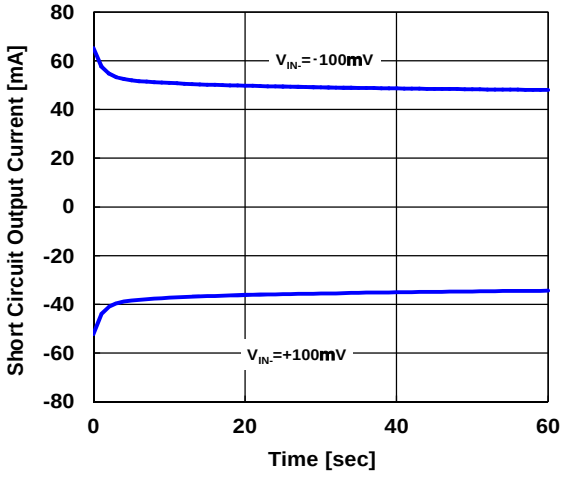
Input Voltage vs. Output Voltage

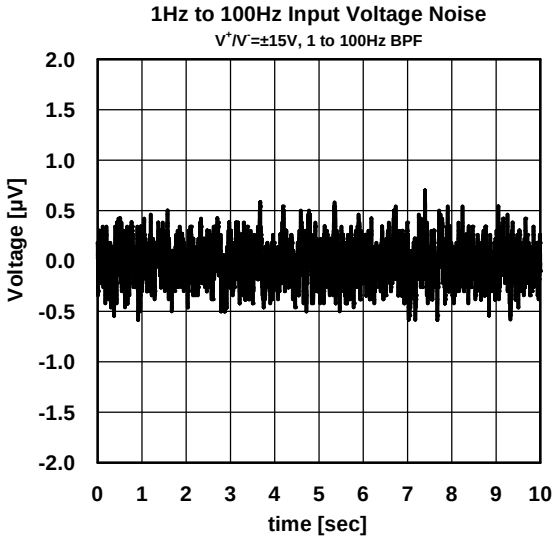
V^+/V^-=±5V, A_V=0dB, R_L=10kΩ

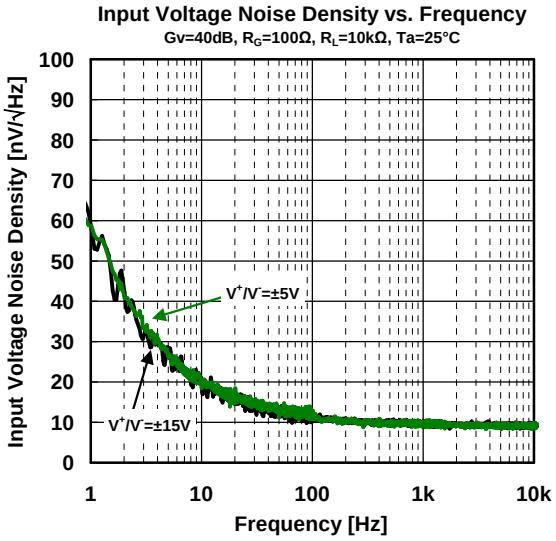


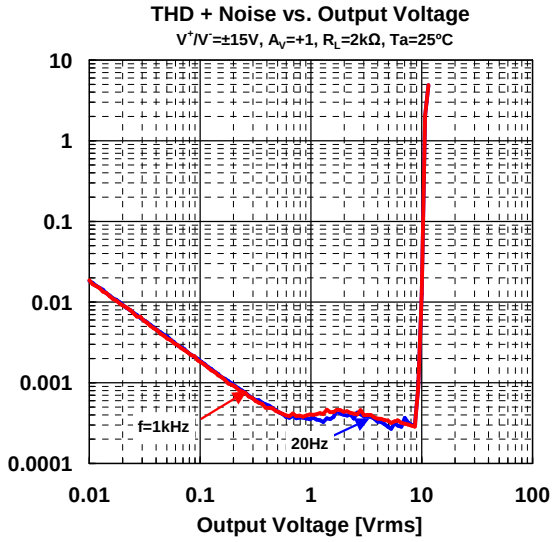
Short Circuit Output Current

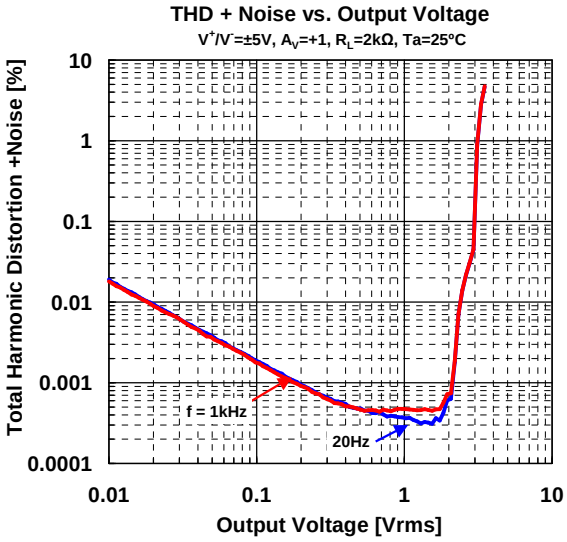
V^+/V^-=±15V, V_{IN+}=0V, V_O=0V, Ta=25ºC




1Hz to 100Hz Input Voltage Noise
V+/V-=±15V, 1 to 100Hz BPF
Voltage [μV]
2.0
1.5
1.0
0.5
0.0
-0.5
-1.0
-1.5
-2.0
0 1 2 3 4 5 6 7 8 9 10
time [sec]

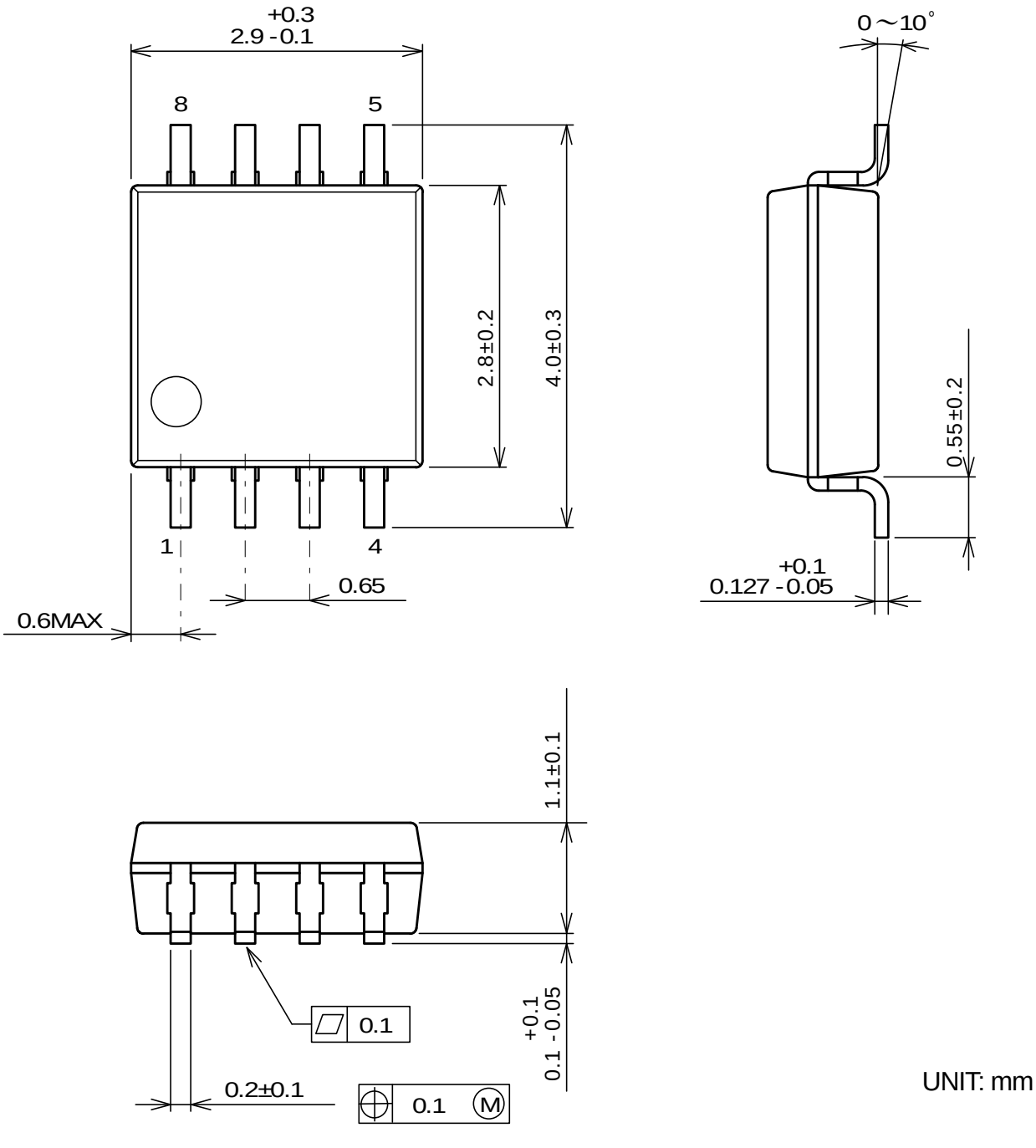

Input Voltage Noise Density vs. Frequency
Gv=40dB, RG=100Ω, RL=10kΩ, Ta=25°C
Input Voltage Noise Density [nV/√Hz]
100
90
80
70
60
50
40
30
20
10
0
V+/V-=±5V
V+/V-=±15V
1 10 100 1k 10k
Frequency [Hz]


THD + Noise vs. Output Voltage
V+/V-=±15V, AV=+1, RL=2kΩ, Ta=25°C
10
1
0.1
0.01
0.001
0.0001
f=1kHz
20Hz
0.01 0.1 1 10 100
Output Voltage [Vrms]


THD + Noise vs. Output Voltage
V+/V-=±5V, AV=+1, RL=2kΩ, Ta=25°C
Total Harmonic Distortion +Noise [%]
10
1
0.1
0.01
0.001
0.0001
f = 1kHz
20Hz
0.01 0.1 1 10
Output Voltage [Vrms]

■PACKAGE DIMENSIONS

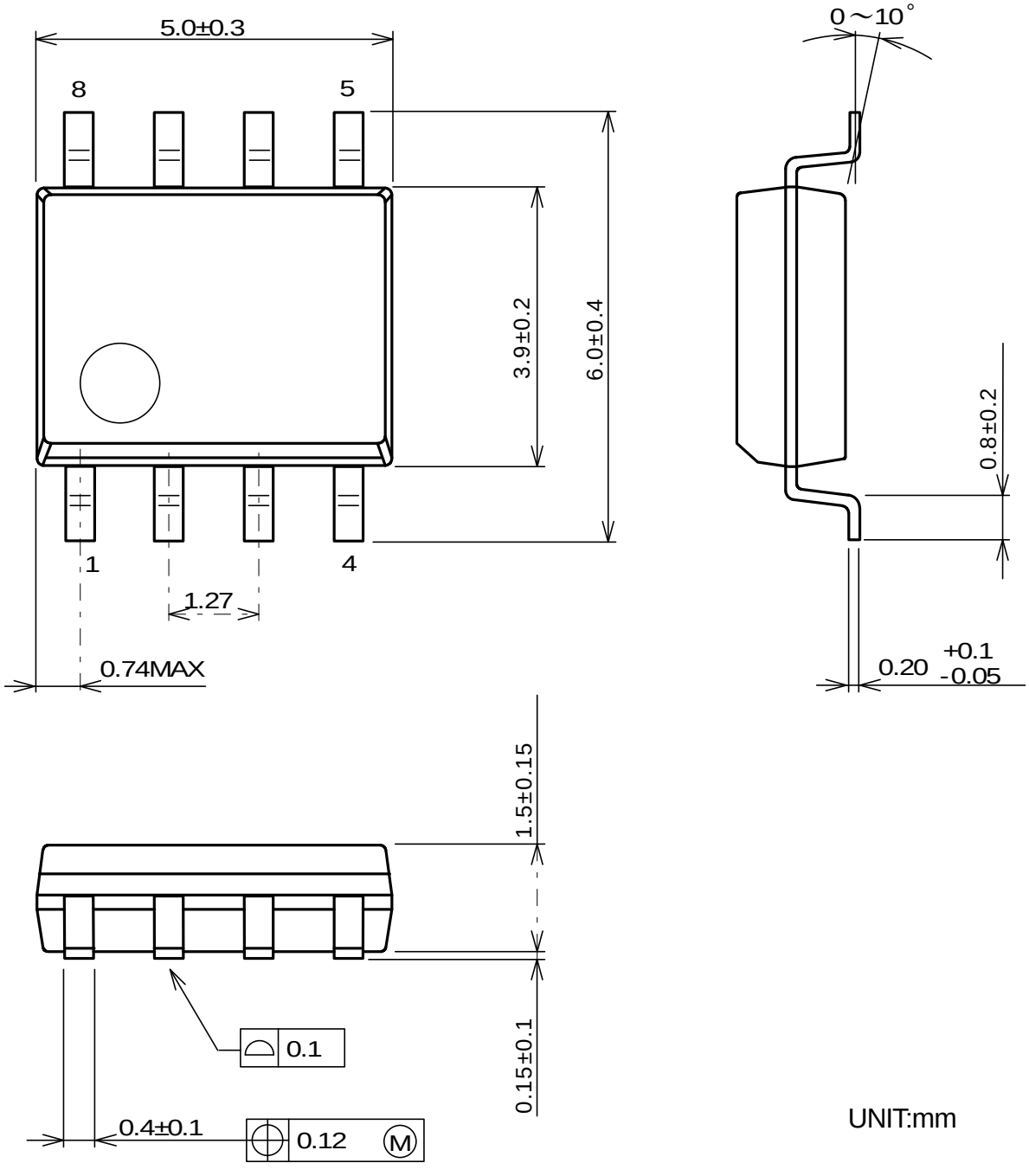
MSOP8(VSP8)



UNIT: mm

■PACKAGE DIMENSIONS

SOP8 JEDEC 150 mil



UNIT:mm

Mouser Electronics

Authorized Distributor

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NJR:

NJM8512AR-TE2 NJM8512BR-TE2

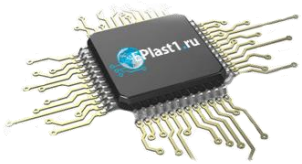
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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